



**MMBF170** 

#### N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

#### **Features**

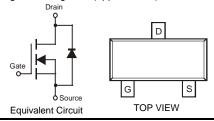
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 2 and 4)

### **Mechanical Data**

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



SOT-23



## **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units		
Drain-Source Voltage		$V_{DSS}$	60	V		
Drain-Gate Voltage $R_{GS} \le 1.0 M\Omega$		$V_{DGR}$	60	V		
Gate-Source Voltage	Continuous Pulsed	V <sub>GSS</sub>	±20 ±40	V		
Drain Current (Note 1)	Continuous Pulsed	I <sub>D</sub>	500 800	mA		

### Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P <sub>d</sub>	300 1.80	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	417	K/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

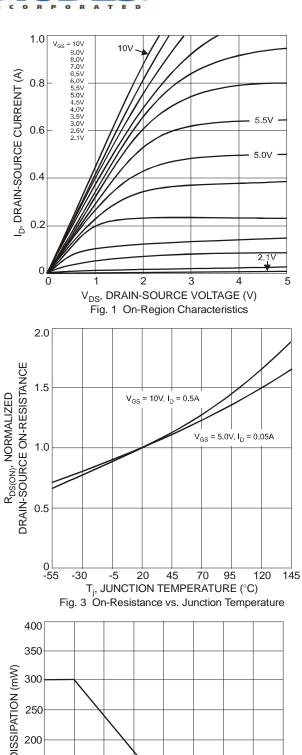
### **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 3)								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	70		V	$V_{GS} = 0V, I_D = 100\mu A$		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			1.0	μA	$V_{DS} = 60V, V_{GS} = 0V$		
Gate-Body Leakage	I <sub>GSS</sub>		_	±10	nA	$V_{GS} = \pm 15V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 3)								
Gate Threshold Voltage	V <sub>GS(th)</sub>	8.0	2.1	3.0	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$		
Static Drain-Source On-Resistance				5.0	Ω	$V_{GS} = 10V, I_D = 200mA$		
Static Dialit-Source Off-Resistance	R <sub>DS</sub> (ON)	_		5.3	5.2	$V_{GS} = 4.5V, I_D = 50mA$		
Forward Transconductance	<b>g</b> FS	80	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$		
DYNAMIC CHARACTERISTICS								
Input Capacitance	C <sub>iss</sub>		22	40	pF			
Output Capacitance	Coss		11	30	pF	$V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz$		
Reverse Transfer Capacitance	C <sub>rss</sub>		2.0	5.0	pF	1		
SWITCHING CHARACTERISTICS								
Turn-On Time	t <sub>on</sub>			10	ns	$V_{DD} = 25V, I_D = 0.5A,$		
Turn-Off Time	t <sub>off</sub>	_		10	ns	$V_{GS} = 10V$ , $R_{GEN} = 50\Omega$		

Notes:

- 1. Device mounted on FR-4 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 2. No purposefully added lead. Halogen and Antimony Free.
- 3. Short duration pulse test used to minimize self-heating effect.
- Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb<sub>2</sub>O<sub>3</sub> Fire Retardants.





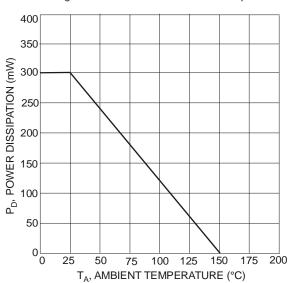
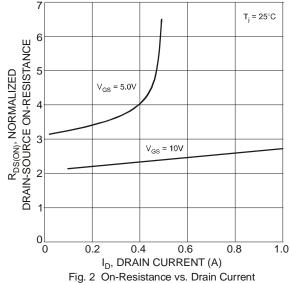


Fig. 5 Max Power Dissipation vs. Ambient Temperature



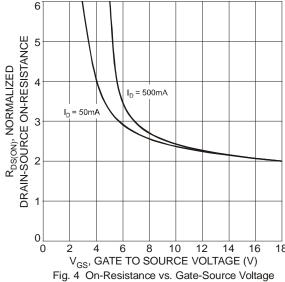


Fig. 4 On-Resistance vs. Gate-Source Voltage

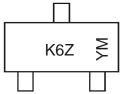


### Ordering Information (Note 5)

Part Number	Case	Packaging
MMBF170-7-F	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

### **Marking Information**

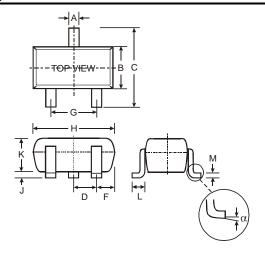


K6Z = Product Type Marking Code YM = Date Code Marking Y = Year ex: N = 2002 M = Month ex: 9 = September

Date Code Key

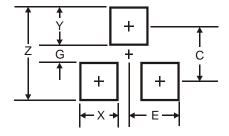
Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	М	N	Р	R	S	Т	U	V	W	Х	Υ	Z
Month	Jan	Fel	b I	Mar	Apr	May	Ju	n	Jul	Aug	Sep	Ос	t I	Nov	Dec
Code	1	2		3	4	5	6	i	7	8	9	0		N	D

## **Package Outline Dimensions**



SOT-23						
Dim	Min	Max				
Α	0.37	0.51				
В	1.20	1.40				
С	2.30	2.50				
D	0.89	1.03				
F	0.45	0.60				
G	1.78	2.05				
Н	2.80	3.00				
J	0.013	0.10				
K	0.903	1.10				
L	0.45 0.61					
M	0.085	0.180				
α	0°	8°				
All Dir	All Dimensions in mm					

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	3.4
G	0.7
Х	0.9
Υ	1.4
С	2.0
E	0.9

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